

SOT223 NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

FZT688B

ISSUE 3 - OCTOBER 1995

FEATURES

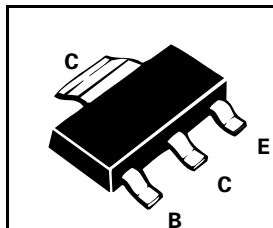
- * Extremely low equivalent on resistance; $R_{CE(sat)}$ **83mΩ at 3A**
- * Gain of 400 at $I_C=3$ Amps and very low saturation voltage

APPLICATIONS

- * Flash gun convertors & Battery powered circuits

PARTMARKING DETAIL - FZT688B

COMPLEMENTARY TYPE - FZT788B



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	10	A
Continuous Collector Current	I_C	4	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	12			V	$I_C=100\mu\text{A}$
	$V_{(BR)CEO}$	12			V	$I_C=10\text{mA}^*$
	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=10\text{V}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.04	V	$I_C=0.1\text{A}, I_B=1\text{mA}$
				0.06	V	$I_C=0.1\text{A}, I_B=0.5\text{mA}^*$
				0.18	V	$I_C=1\text{A}, I_B=50\text{mA}^*$
				0.35	V	$I_C=3\text{A}, I_B=20\text{mA}^*$
				0.40	V	$I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=3\text{A}, I_B=20\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=3\text{A}, V_{CE}=2\text{V}$
Static Forward Current Transfer Ratio	h_{FE}	500				$I_C=0.1\text{A}, V_{CE}=2\text{V}^*$
		400				$I_C=3\text{A}, V_{CE}=2\text{V}^*$
		100				$I_C=10\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	C_{obo}		40		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on} t_{off}		40		ns	$I_C=500\text{mA}, I_{B1}=50\text{A}$
			500		ns	$I_{B2}=50\text{mA}, V_{CC}=10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

FZT688B

TYPICAL CHARACTERISTICS

